

Chapt8Fig14a.m

Total Elastic Ionized Impurity Scattering Rate

Thomas-Fermi Screening with Angular Integration

Semiconductor Physics Documentation

Abstract

This document provides complete theoretical background and code analysis for `Chapt8Fig14a.m`, which calculates the total elastic scattering rate due to ionized impurities as a function of electron energy. The code employs Thomas-Fermi screening and numerical angular integration using the trapezoidal rule.

Contents

1	Theoretical Foundation	2
1.1	Ionized Impurity Scattering Theory	2
1.2	Total Scattering Rate	2
1.3	Change of Variables	2
1.4	Thomas-Fermi Screening	2
2	Numerical Method: Trapezoidal Integration	3
2.1	The Trapezoidal Rule	3
2.2	Application to Angular Integration	3
3	Line-by-Line Code Analysis	3
3.1	Function Declaration	3
3.2	Physical Constants	3
3.3	Carrier Density Loop	4
3.4	Thomas-Fermi Screening Wavevector	4
3.5	Fermi Energy	4
3.6	Constant Prefactor	4
3.7	Energy Grid Setup	4
3.8	Main Energy Loop	5
3.9	Angular Integration Loop	5
3.10	Store Results	5
3.11	Helper Function: <code>gchil</code>	5
3.12	Plotting	5
4	Physical Interpretation	6
4.1	Energy Dependence	6
4.2	Density Dependence	6
5	Summary	6

1 Theoretical Foundation

1.1 Ionized Impurity Scattering Theory

Axiom 1 (Fermi's Golden Rule for Scattering). *The scattering rate from state \mathbf{k} to state \mathbf{k}' is:*

$$W_{\mathbf{k} \rightarrow \mathbf{k}'} = \frac{2\pi}{\hbar} |V_{\mathbf{k}\mathbf{k}'}|^2 \delta(E_{\mathbf{k}'} - E_{\mathbf{k}}) \quad (1)$$

Definition 1 (Screened Coulomb Matrix Element). *For ionized impurity scattering with Thomas-Fermi screening:*

$$V_{\mathbf{k}\mathbf{k}'} = \frac{e^2}{\varepsilon_0 \varepsilon_r} \cdot \frac{1}{q^2 + q_{TF}^2} \quad (2)$$

where $q = |\mathbf{k}' - \mathbf{k}|$ is the momentum transfer.

1.2 Total Scattering Rate

Theorem 1 (Total Elastic Scattering Rate). *The total scattering rate is obtained by integrating over all final states:*

$$\frac{1}{\tau(E)} = \sum_{\mathbf{k}'} W_{\mathbf{k} \rightarrow \mathbf{k}'} = n_i \int |V(q)|^2 g(\mathbf{k}') \delta(E' - E) d^3k' \quad (3)$$

where n_i is the impurity concentration.

Theorem 2 (Angular Integration Form). *For elastic scattering on a spherical Fermi surface:*

$$\frac{1}{\tau(E)} = \frac{\pi n_i m^*}{\hbar^3 k^3} \left(\frac{e^2}{4\pi \varepsilon_0 \varepsilon_r} \right)^2 \int_0^\pi \frac{\sin \theta}{(q^2 + q_{TF}^2)^2} d\theta \quad (4)$$

where $q = 2k \sin(\theta/2)$.

1.3 Change of Variables

Lemma 1 (Substitution to η). *With $\eta = \sin(\theta/2)$:*

- $q = 2k\eta$
- $d\eta = \frac{1}{2} \cos(\theta/2) d\theta$
- $\sin \theta = 2 \sin(\theta/2) \cos(\theta/2) = 2\eta \sqrt{1 - \eta^2}$

The integral becomes:

$$\int_0^\pi \frac{\sin \theta}{(q^2 + q_{TF}^2)^2} d\theta = \int_0^1 \frac{4\eta \sqrt{1 - \eta^2}}{(4k^2 \eta^2 + q_{TF}^2)^2} \cdot \frac{2d\eta}{\sqrt{1 - \eta^2}} \quad (5)$$

1.4 Thomas-Fermi Screening

Definition 2 (Thomas-Fermi Wavevector).

$$q_{TF}^2 = \frac{k_F m^* e^2}{\pi^2 \hbar^2 \varepsilon_0 \varepsilon_r} \quad (6)$$

where $k_F = (3\pi^2 n)^{1/3}$ is the Fermi wavevector.

2 Numerical Method: Trapezoidal Integration

2.1 The Trapezoidal Rule

Theorem 3 (Trapezoidal Rule). *For a function $f(x)$ on interval $[a, b]$ with N subintervals of width $h = (b - a)/N$:*

$$\int_a^b f(x) dx \approx h \left[\frac{f(a) + f(b)}{2} + \sum_{i=1}^{N-1} f(a + ih) \right] \quad (7)$$

Theorem 4 (Error Estimate). *The error in the trapezoidal rule is:*

$$E_T = -\frac{(b - a)^3}{12N^2} f''(\xi) \quad (8)$$

for some $\xi \in [a, b]$. The method is second-order accurate: $E_T = O(h^2)$.

2.2 Application to Angular Integration

The code uses a simplified form where the step size equals the increment:

$$\int_0^\pi f(\theta) d\theta \approx \sum_{j=1}^{180} f(\theta_j) \cdot \Delta\theta \quad (9)$$

where $\Delta\theta = \pi/180$ radians (1° steps).

3 Line-by-Line Code Analysis

3.1 Function Declaration

```
1 function TFelasticScattering
2 clear; clf;
```

Declares as a function and clears workspace.

3.2 Physical Constants

```
1 m0=9.109382e-31;
2 echarge=1.6021764e-19;
3 hbar=1.05457159e-34;
4 epsilon0=8.8541878e-12;
```

$$m_0, e, \hbar, \varepsilon_0 \quad (10)$$

Fundamental physical constants in SI units.

```
1 ezero=13.2;
2 m1=0.070;
```

$$\varepsilon_r = 13.2, \quad m^* = 0.07m_0 \quad (11)$$

GaAs material parameters.

```
1 emax=300.0d-3;
2 n=1.0d16;
3 npoints = 200;
```

$$E_{\max} = 300 \text{ meV}, \quad n_{\text{initial}} = 10^{16} \text{ cm}^{-3} \quad (12)$$

Maximum energy for plot and starting carrier density.

3.3 Carrier Density Loop

```
1 for k=1:2
2   n=n*10;
```

$$n \in \{10^{17}, 10^{18}\} \text{ cm}^{-3} \quad (13)$$

Loop over two carrier densities (plotted as two curves).

```
1 kF1=(3*(pi^2)*n)^(1/3);
2 kF1=kF1*1.e2;
```

$$k_F = (3\pi^2 n)^{1/3} \times 10^2 \text{ (convert cm}^{-1} \rightarrow \text{m}^{-1}) \quad (14)$$

Fermi wavevector calculation and unit conversion.

```
1 kF2=kF1^2;
2 kF3=kF1^3;
```

$$k_F^2, k_F^3 \quad (15)$$

Powers of Fermi wavevector for later use.

3.4 Thomas-Fermi Screening Wavevector

```
1 qTF2=kF1*m0*m1*(echarge^2)/(epsilon0*ezero*(pi^2)*(hbar^2));
```

$$q_{\text{TF}}^2 = \frac{k_F m_0 m_1 e^2}{\epsilon_0 \epsilon_r \pi^2 \hbar^2} \quad (16)$$

Thomas-Fermi wavevector squared.

3.5 Fermi Energy

```
1 eF=((hbar*kF1)^2)/(2.0*m0*m1*echarge);
```

$$E_F = \frac{(\hbar k_F)^2}{2m^*} \cdot \frac{1}{e} \text{ [eV]} \quad (17)$$

Fermi energy in eV (division by e converts from J to eV).

3.6 Constant Prefactor

```
1 const=(pi*n*1.0e6*(echarge^4)*m0*m1);
2 const=const/(((4.*pi*epsilon0)^2)*(ezero^2)*(hbar^3));
```

$$C = \frac{\pi n \cdot 10^6 \cdot e^4 \cdot m_0 m_1}{(4\pi\epsilon_0)^2 \epsilon_r^2 \hbar^3} \quad (18)$$

Prefactor for scattering rate (includes unit conversion).

3.7 Energy Grid Setup

```
1 emin=eF;
2 demax=(emax-emin)/200.0;
3 dth=pi/180.0;
```

$$E_{\min} = E_F, \quad \Delta E = \frac{E_{\max} - E_F}{200}, \quad \Delta\theta = \frac{\pi}{180} \quad (19)$$

Energy step and angular step (1° increments).

3.8 Main Energy Loop

```

1 ei=emin;
2 for i=1:npoints
3     ei=ei+demax;
4     ak=(sqrt(2.*m0*m1*ei*echarge))/hbar;
5     ak3=ak^3;

```

$$k = \frac{\sqrt{2m^*E \cdot e}}{\hbar}, \quad k^3 \quad (20)$$

Electron wavevector at each energy.

3.9 Angular Integration Loop

```

1 aint1=0.0;
2 theta=0.0;
3 for j=1:180
4     theta=theta+dth;
5     aint1=aint1+(dth*gchi1(theta,ak,qTF2));
6 end

```

$$I = \sum_{j=1}^{180} g(\theta_j) \cdot \Delta\theta \quad (21)$$

Trapezoidal integration over angle (calls helper function gchi1).

3.10 Store Results

```

1 y1(i)=const*aint1/ak3;
2 x1(i)=ei*1.d3;

```

$$\frac{1}{\tau(E)} = \frac{C \cdot I}{k^3}, \quad E \text{ [meV]} \quad (22)$$

Scattering rate calculation and energy in meV.

3.11 Helper Function: gchi1

```

1 function gchi1 = gchi1(theta,k,qTF2)
2 x=2.0*k*sin(theta/2.0);
3 x2=x^2;
4 g=(tan(theta/2.0))*((sin(theta/2.0))^2)*((1.0+(qTF2/x2))^2);
5 gchi1=1.0/g;
6 return

```

$$g(\theta) = \frac{1}{\tan(\theta/2) \cdot \sin^2(\theta/2) \cdot (1 + q_{\text{TF}}^2/q^2)^2} \quad (23)$$

where $q = 2k \sin(\theta/2)$.

This computes the integrand for the angular integration.

3.12 Plotting

```

1 figure(1);hold on;plot(x1,y1,'r');axis([0,emax*1.d3,0,16e12]);

```

Plot scattering rate vs energy with axis limits.

4 Physical Interpretation

4.1 Energy Dependence

The scattering rate $1/\tau(E)$ typically:

- Decreases with increasing energy (faster electrons harder to scatter)
- Scales approximately as $E^{-3/2}$ at high energy
- Has a plateau or peak near E_F

4.2 Density Dependence

Higher carrier density leads to:

- Stronger screening (larger q_{TF})
- Lower scattering rate at small angles
- But higher overall scattering due to more impurities (if $n_i = n$)

5 Summary

This code calculates the total elastic scattering rate by numerically integrating over all scattering angles using the trapezoidal rule. The helper function `gchi1` encodes the screened Coulomb scattering matrix element with Thomas-Fermi screening. Results show how scattering rate varies with electron energy and carrier density.